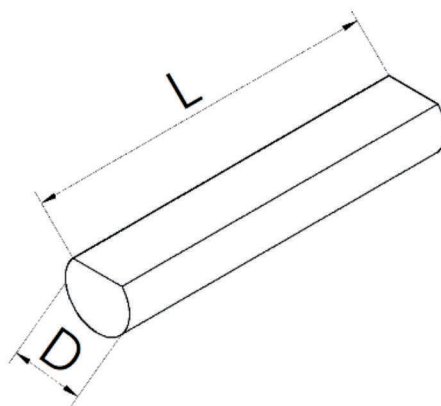


磷化铟 (InP) 多晶

Indium phosphide Polycrystalline

磷化铟是重要的III-V族化合物半导体材料, 由高纯红磷和高纯铟合成, 是新一代光电子功能基础材料。

InP is an important semiconductor material of III-V compound, which is synthesized by high-purity red phosphorus and high-purity indium. It is an advanced base material for the new generation optoelectronic field.



产品规格: Specifications:

供货状态: 不定尺棒料/块/片状;

Product Shape: Ingot / Ingot section/ Slices

棒料尺寸: D: ~75mm, L: Max. 450mm;

Ingot Dimensions: D: ~75mm, L: Max. 450mm

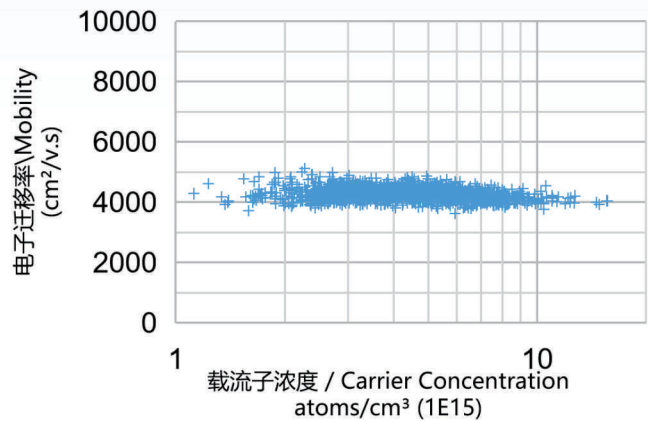
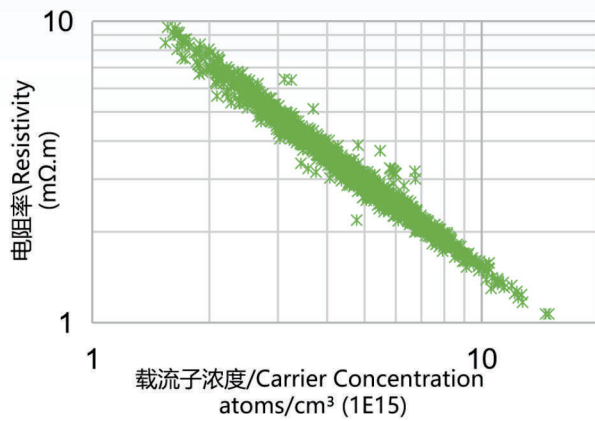
单锭重量: Max. 8Kg;

Ingot Weight: Max. 8Kg;

产品等级 Product Grade	载流子浓度 (atoms/cm ³) Carrier Concentration atoms/cm ³
特级 / Gr. P	≤3E15
一级 / Gr. 1	≤6E15
二级 / Gr. 2	≤1E16
三级 / Gr. 3	≤2E16
四级 / Gr. 4	≤3E16

产品电学参数

Product Parameters:



GDMS

元素 Element	含量 ppm wt	元素 Element	含量 ppm wt	元素 Element	含量 ppm wt
Li	<0.001	As	<0.01	Sm	<0.001
Be	<0.001	Se	<0.005	Eu	<0.005
B	<0.005	Br	<0.005	Gd	<0.005
F	<0.005	Rb	<0.001	Tb	<0.001
Na	<0.005	Sr	<0.001	Dy	<0.005
Mg	<0.005	Y	<0.001	Ho	<0.001
Al	<0.001	Zr	<0.001	Er	<0.001
Si	0.002	Nb	<0.01	Tm	<0.001
P	Matrix	Mo	<0.005	Yb	<0.001
S	<0.005	Ru	<0.005	Lu	<0.001
Cl	<0.005	Rh	<0.001	Hf	<0.001
K	<0.005	Pd	<0.001	Ta	Source
Ca	<0.005	Ag	<0.05	W	<0.005
Sc	<0.005	Cd	<0.01	Re	<0.001
Ti	<0.005	In	Matrix	Os	<0.001
V	<0.001	Sn	<0.005	Ir	<0.001
Cr	<0.001	Sb	<0.005	Pt	<0.001
Mn	<0.001	Te	<0.005	Au	<0.005
Fe	<0.001	I	<0.005	Hg	<0.001
Co	<0.001	Cs	<0.005	Tl	<0.005
Ni	<0.001	Ba	<0.001	Pb	<0.001
Cu	<0.005	La	<0.001	Bi	<0.001
Zn	<0.005	Ce	<0.001	Th	<0.0001
Ga	<0.01	Pr	<0.001	U	<0.0001
Ge	<0.005	Nd	<0.001		



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